(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
21 August 2008 (21.08.2008)

PCT

(10) International Publication Number
WO 2008/099245 A1

(51) International Patent Classification:
H01L 21/306 (2006.01) *H01L 21/762* (2006.01)
H01L 21/20 (2006.01)

(21) International Application Number:
PCT/IB2008/000156

(22) International Filing Date: 23 January 2008 (23.01.2008)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
0753284 15 February 2007 (15.02.2007) FR

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(81) Designated States *(unless otherwise indicated, for every kind of national protection available)*: AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, SV, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

(84) Designated States *(unless otherwise indicated, for every kind of regional protection available)*: ARIPO (BW, GH,

[Continued on next page]

(54) Title: METHOD FOR POLISHING HETEROSTRUCTURES

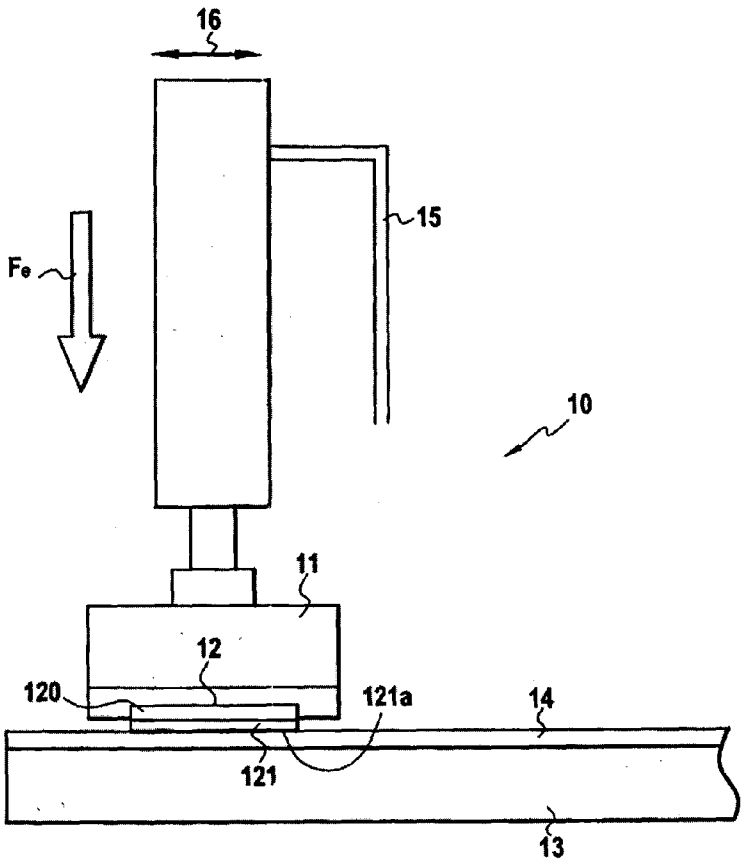


FIG.1

(57) Abstract: A polishing method of a heterostructure (12) comprising at least one relaxed superficial heteroepitaxial layer (121) on a substrate (120) made from a different material from that of said heteroepitaxial layer. The method comprises a first chemical mechanical polishing step of the surface of the heteroepitaxial layer (12) performed with a polishing cloth (14) having a first compressibility ratio and with a polishing solution having a first silica particle concentration. The first chemical mechanical polishing step is followed by a second chemical mechanical polishing step of the surface of the heteroepitaxial layer (121), said second step being performed with a polishing cloth having a second compressibility ratio, higher than said first compressibility ratio, and with a polishing solution having a second silica particle concentration, lower than said first concentration.

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GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MT, NL, NO, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Declaration under Rule 4.17:
— *of inventorship (Rule 4.17(iv))*

Published:
— *with international search report*